

Amendments of the Claims

The following list of claims replaces all previous version(s) of claims.

1 -7. Canceled.

8. (currently amended) A method of forming a patterned material structure on a substrate, said method comprising:

(A) providing a substrate with a layer of said material wherein said material is chromium-containing metal composition,

(B) applying a resist composition to said substrate to form a resist layer on said substrate, said resist composition comprising

a) an imaging polymer,

b) acid-labile moieties,

c) a radiation-sensitive acid generator, and

d) a base additive component, wherein said base additive component comprises:

(i) a room temperature solid base selected from the group consisting of aromatic amines and imidazoles, and

(ii) a liquid low vapor pressure base selected from the group consisting of triethanolamine, ~~1-naphthylamine, 2-naphthylamine, diphenylamine, acetanilide, 3,6,9-triazaundecamethylenediamine, and 4,4'-propane 1,3-diylbismorpholine, wherein a mole ratio of said low vapor pressure base to said solid base is in the range of 0.15 to 0.5.~~

(C) patternwise exposing said substrate to electron beam radiation whereby acid is generated by radiation-sensitive acid generator in exposed regions of said resist layer,

(D) forming ~~developing~~ a patterned resist structure having a profile with minimal footing in ~~said resist layer~~ by removing radiation-exposed portions of said resist, and

(E) transferring resist structure pattern to said material layer by removing portions of said material layer through spaces in said resist structure pattern.

9. Canceled.

10. (currently amended) The method of claim 8 wherein said acid-labile protecting group is a moiety selected from the group consisting of ketals, ~~acetals~~ and orthoesters.

11. (currently amended) The method of claim 8 wherein said transfer of ~~[[step (F)]]~~ step (E) comprises reactive ion etching.

12. (original) The method of claim 8 wherein at least one intermediate layer is provided between said material layer and said resist layer, and step (E) comprises etching through said intermediate layer.

13. (original) The method of claim 8 wherein said resist is thermally treated between steps (C) and (D).

14 - 19. Canceled.